

Appl. No. 10/050,334

Please replace the Abstract with the following clean replacement paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

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—A capacitor fabrication method may include forming a first capacitor electrode over a substrate, the first electrode having an inner surface area per unit area and an outer surface area per unit area that are both greater than an outer surface area per unit area of the substrate. A capacitor dielectric layer and a second capacitor electrode may be formed over the dielectric layer. The method may further include forming rugged polysilicon over the substrate, the first electrode being over the rugged polysilicon. Accordingly, the outer surface area of the first electrode can be at least 30% greater than the outer surface area of the substrate without the first electrode including polysilicon.—

In the Claims

Please replace claims 16 and 18 with the following clean version of the amended claims, in accordance with 37 C.F.R. § 1.121(c)(1)(i). Cancel all previous versions of any amended claim.

A marked up version showing amendments to any claims being changed is provided in one or more accompanying pages separate from this amendment in accordance with 37 C.F.R. § 1.121(c)(1)(ii). Any claim not accompanied by a marked up version has not been changed relative to the immediate prior version, except that marked up versions are not being supplied for any added claim or canceled claim.

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16. (amended) A capacitor construction comprising:

a surface area enhancement layer over a substrate, the enhancement layer having an outer surface area per unit area that is greater than an inner surface area per unit area of the enhancement layer;

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a first capacitor electrode over the enhancement layer, the first electrode having an inner surface area per unit area and an outer surface area per unit area that are both greater than an outer surface area per unit area of the substrate, and the first electrode not comprising the enhancement layer;

a capacitor dielectric layer over the first electrode; and

a second capacitor electrode over the dielectric layer.

18. (amended) The construction of claim 16 wherein the enhancement layer

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comprises rugged polysilicon over the substrate, the first electrode being over the rugged polysilicon.